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Thank you for your cooperation and understanding,

WeEn Semiconductors



# **TYN16-600CT**



SCR

Rev. 1 — 20 March 2012

**Product data sheet** 

# 1. Product profile

#### 1.1 General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high thermal cycling performance and high junction temperature capability ( $T_{i(max)} = 150$  °C).

#### 1.2 Features and benefits

- High junction operating temperature capability
- High thermal cycling performance
- High voltage capability
- Planar passivated for voltage ruggedness and reliability

### 1.3 Applications

- Ignition circuits
- Motor control

- Protection circuits e.g. SMPS inrush current
- Voltage regulation

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 10  \text{ms}$ ; see Figure 4; see Figure 5	-	-	180	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 8.3 \text{ ms}$	-	-	198	Α
Tj	junction temperature		-	-	150	°C
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>mb</sub> ≤ 133 °C; see <u>Figure 3</u>	-	-	10.2	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 133 °C; see Figure 1; see Figure 2	-	-	16	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 7</u>	-	-	15	mA
Dynamic cha	rateristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		. 51
2	Α	anode	mb	A <del>    K</del> G
3	G	gate		sym037
mb	A	mounting base; connected to anode	1 2 3	
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN16-600CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>mb</sub> ≤ 133 °C; see <u>Figure 3</u>	-	10.2	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 133 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	16	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; see Figure 4; see Figure 5	-	180	Α
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms	-	198	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	$t_p = 10 \text{ ms}$ ; sine-wave pulse	-	162	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 40 \text{ A}; I_G = 200 \text{ mA};$ $dI_G/dt = 200 \text{ mA}/\mu\text{s}$	-	50	A/μs
I <sub>GM</sub>	peak gate current		-	4	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	10	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

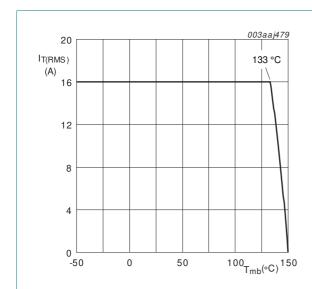
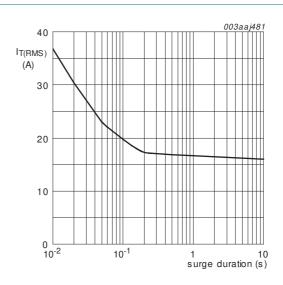


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 133 \text{ }^{\circ}\text{C}$ 

Fig 2. RMS on-state current as a function of surge duration; maximum values

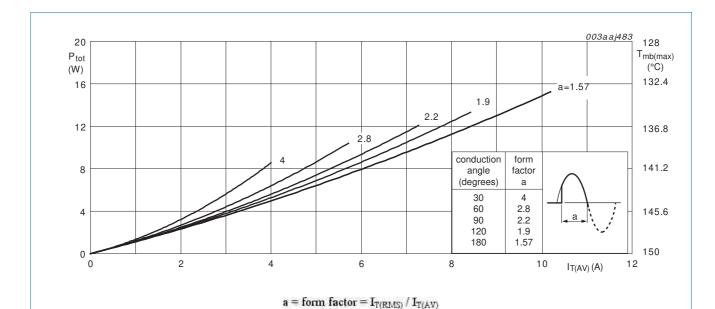


Fig 3. Total power dissipation as a function of average on-state current; maximum values

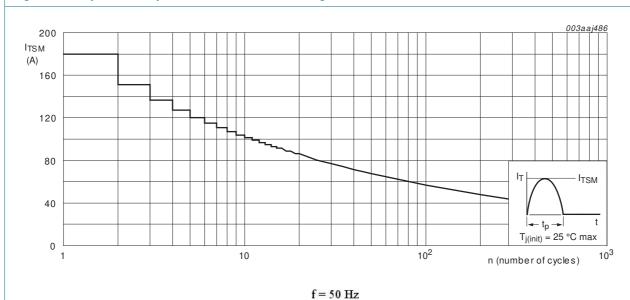
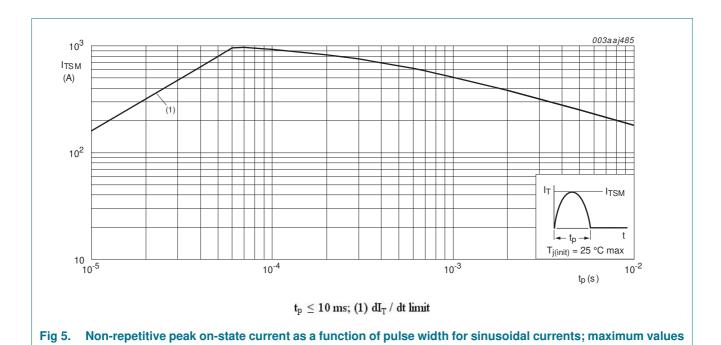


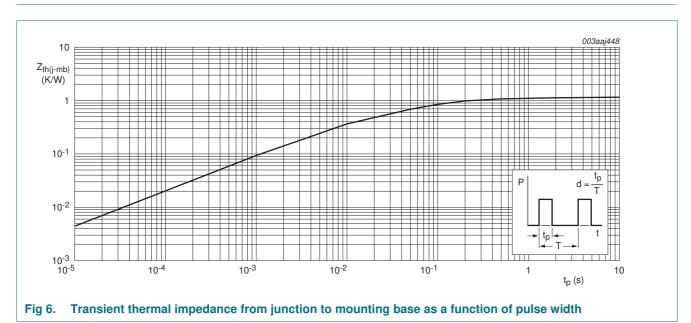
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



# 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 6	-	-	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



# 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 7</u>	-	-	15	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	-	60	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	40	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 32 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	1.2	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	0.7	1.3	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 11</u>	0.2	0.4	-	V
I <sub>D</sub>	off-state current	$V_D = 600 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	0.2	1	mA
I <sub>R</sub>	reverse current	$T_j = 150  ^{\circ}\text{C};  V_R = 600  \text{V}$	-	0.2	1	mA
Dynamic ch	narateristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs

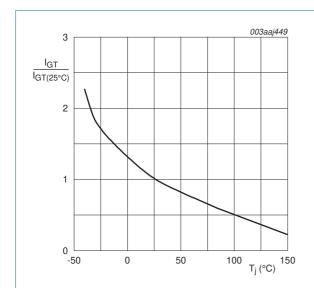


Fig 7. Normalized gate trigger current as a function of junction temperature

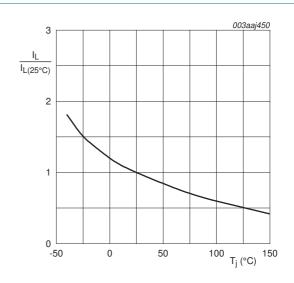
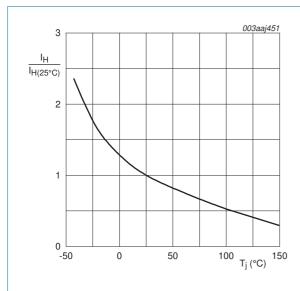
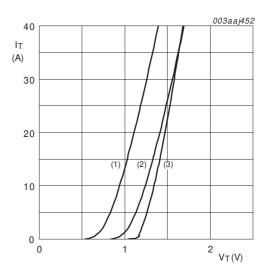


Fig 8. Normalized latching current as a function of junction temperature





 $V_o = 1.08 \text{ V}; R_s = 0.0165 \Omega$ 

(1) T<sub>j</sub> = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

Fig 10. On-state current as a function of on-state voltage

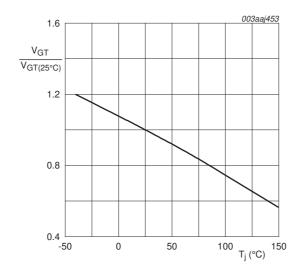
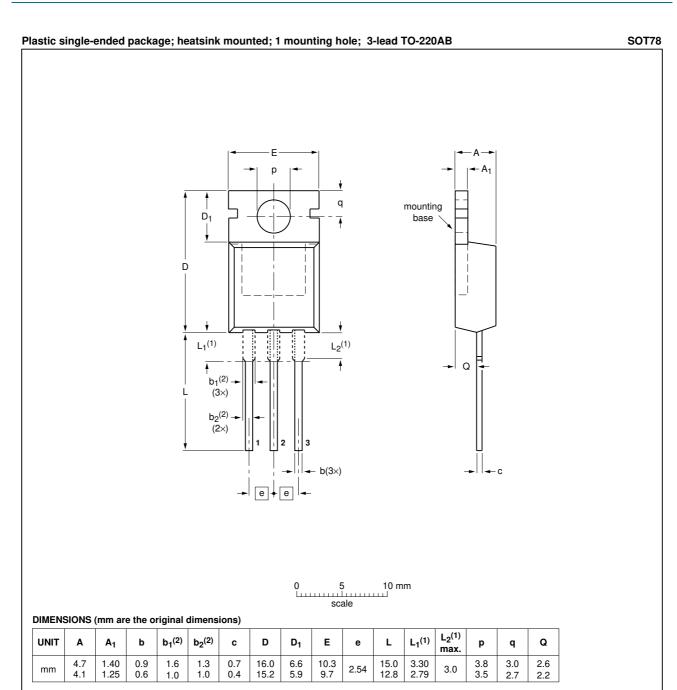


Fig 11. Normalized gate trigger voltage as a function of junction temperature

# 7. Package outline



#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13	

Fig 12. Package outline SOT78 (TO-220AB)

TYN16-600CT

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# **Revision history**

#### Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
TYN16-600CT v.1	20120320	Product data sheet	-	-

# 9. Legal information

#### 9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# 11. Contents

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